

Features

- For surface mount applications
- Glass passivated chip junction
- Ideal for automated placement
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directive

SOD-323W



1.Cathode —|<— 2.Anode

Marking Code: T4

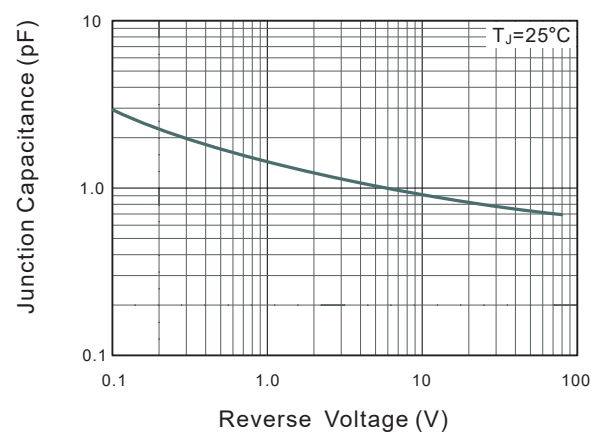
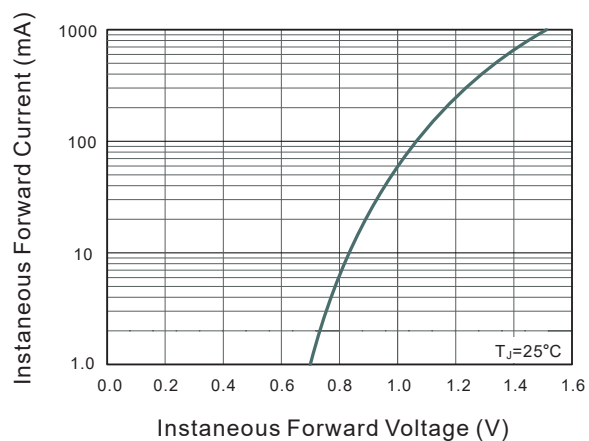
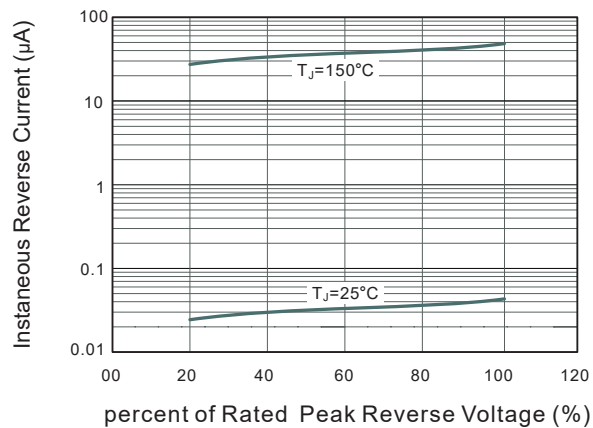
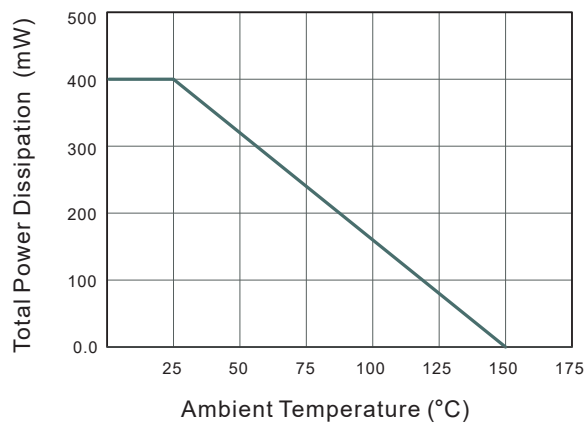
Absolute Maximum Ratings at $T_A = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	1N4148WB	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Maximum RMS voltage	V_{RMS}	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current at $t = 1\text{ s}$ at $t = 1\text{ ms}$ at $t = 1\text{ }\mu\text{s}$	I_{FSM}	0.5 1 4	A
Maximum Power Dissipation	P_D	400	mW
Operating Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	1N4148WB	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ }\mu\text{A}$	$V_{(BR)R}$	75	V
Maximum Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.715 0.855 1.00 1.25	V
Peak Reverse Current at $V_R = 20\text{ V}, T_J = 25\text{ }^{\circ}\text{C}$ at $V_R = 75\text{ V}, T_J = 25\text{ }^{\circ}\text{C}$ at $V_R = 25\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$ at $V_R = 75\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$	I_R	0.025 1 30 50	μA
Typical Junction Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_j	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R, I_F = I_R = 10\text{ mA}, R_L = 100\text{ }\Omega$	T_{rr}	4	nS

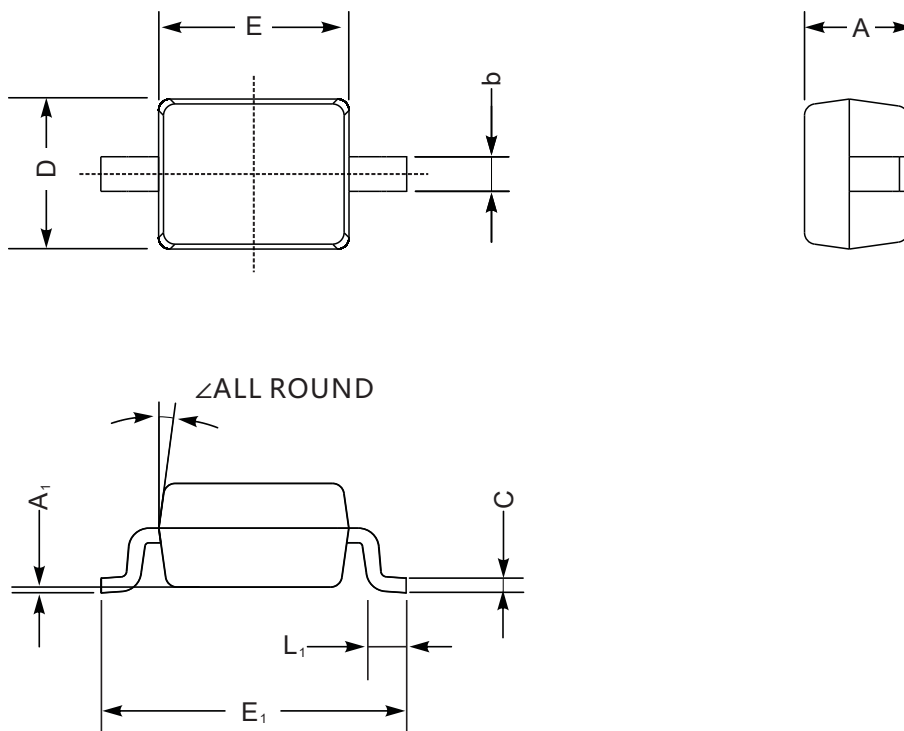
Typical Characteristic Curves



Package Outline

SOD-323W

Dimensions in mm



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	